

## 描述 / Descriptions

SOP-8 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a SOP-8 Plastic Package.

## 特征 / Features

低导通电阻，低输入电容，开关速度快。

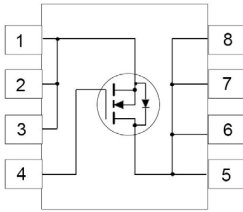
Low On-Resistance, Low Input Capacitance, Fast Switching Speed.

## 用途 / Applications

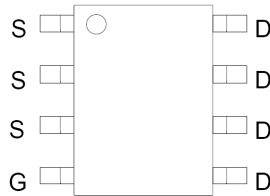
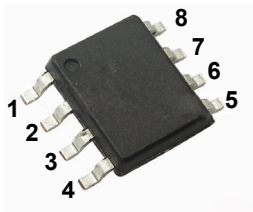
适用于负荷开关，转换开关。

Load Switch, Adaptor Switch.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1、PIN 2、PIN 3 : S

PIN 4 : G

PIN5、PIN 6、PIN 7、PIN 8 : D

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit	
Drain-Source Voltage		$V_{DSS}$	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
continuous Drain Current (Note 6) $V_{GS} = 10V$	Steady State	$I_D$	( $T_a = 25^\circ C$ )	9.2	A
			( $T_a = 70^\circ C$ )	7.4	A
	$t < 10s$	$I_D$	( $T_a = 25^\circ C$ )	11.9	A
			( $T_a = 70^\circ C$ )	9.5	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	Steady State	$I_D$	( $T_a = 25^\circ C$ )	7.5	A
			( $T_a = 70^\circ C$ )	6.0	A
	$t < 10s$	$I_D$	( $T_a = 25^\circ C$ )	9.7	A
			( $T_a = 70^\circ C$ )	7.7	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)		$I_{DM}$	60	A	
Maximum Continuous Body Diode Forward Current (Note 6)		$I_S$	2	A	
Avalanche Current (note7)L=0.1mH		$I_{AS}$	15.3	A	
Avalanche Energy (note7)L=0.1mH		$E_{AS}$	11.7	mJ	
Power Dissipation (note5)		$P_D$	1.5	W	
Thermal Resistance, Junction-to-Ambient (note5)	Steady State	$R_{\theta JA}$	85	°C/W	
	$t < 10s$		45	°C/W	
Power Dissipation (note6)		$P_D$	2.1	W	
Thermal Resistance, Junction-to-Ambient (note6)	Steady State	$R_{\theta JA}$	74	°C/W	
	$t < 10s$		37	°C/W	
Thermal Resistance, Junction-to case		$R_{\theta JC}$	13	°C/W	
Operating and Junction Temperature Range		$T_j \quad T_{stg}$	-55~150	°C	

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage(note8)	$V_{DSS}$	$V_{GS}=0V$	$I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current(note8)	$I_{DSS}$	$V_{DS}=48V$	$V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward(note8)	$I_{GSS}$	$V_{GS}=\pm 20V$	$V_{DS}=0V$			±100	nA
Gate Threshold Voltage(note8)	$V_{GS(th)}$	$V_{DS}=V_{GS}$	$I_D=250\mu A$	1.0		2.5	V
Static Drain-Source On-Resistance(note8)	$R_{DS(on)}$	$V_{GS}=10V$	$I_D=10A$			18	mΩ
		$V_{GS}=4.5V$	$I_D=6.0A$			28	mΩ
Diode Forward Voltage(note7)	$V_{SD}$	$I_S=1.0A$	$V_{GS}=0V$		0.7	1.2	V

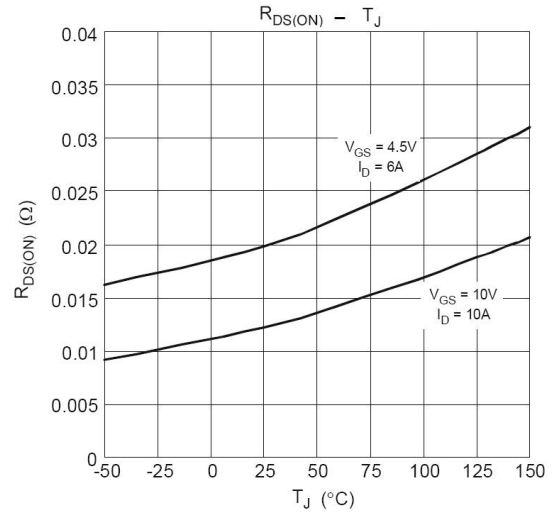
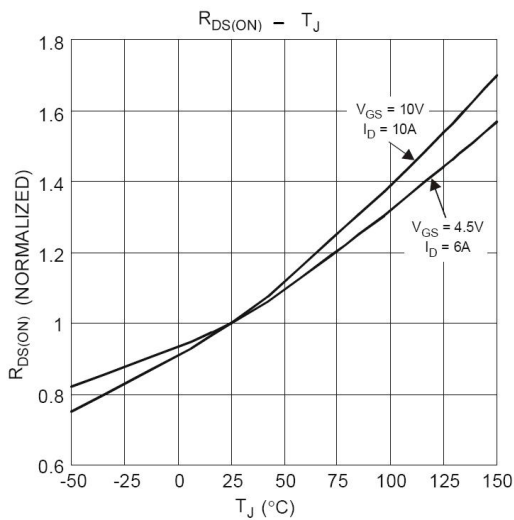
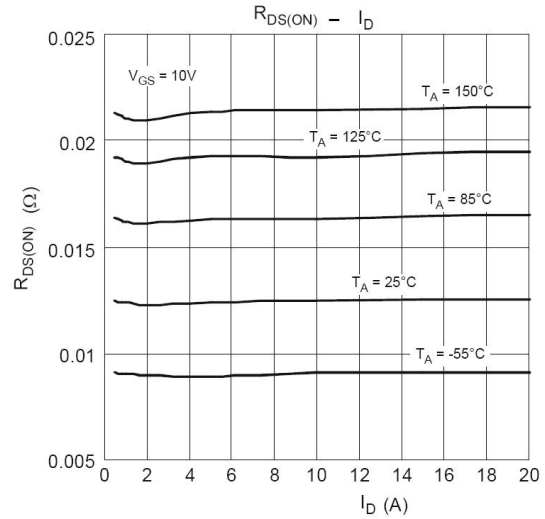
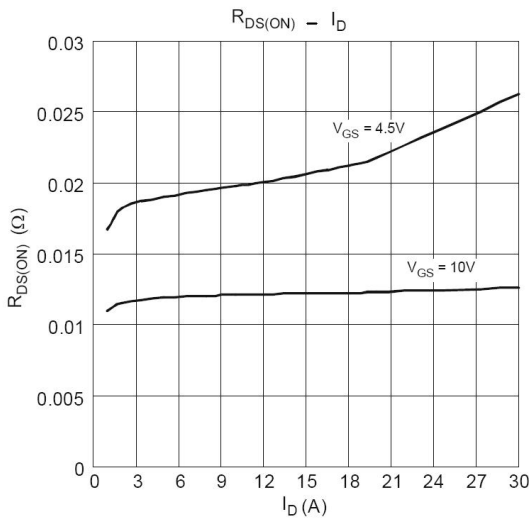
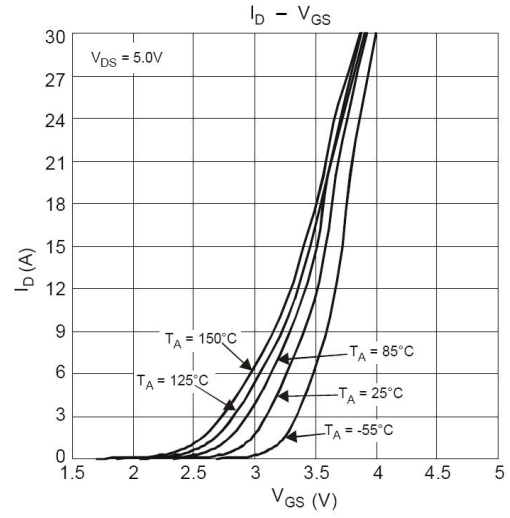
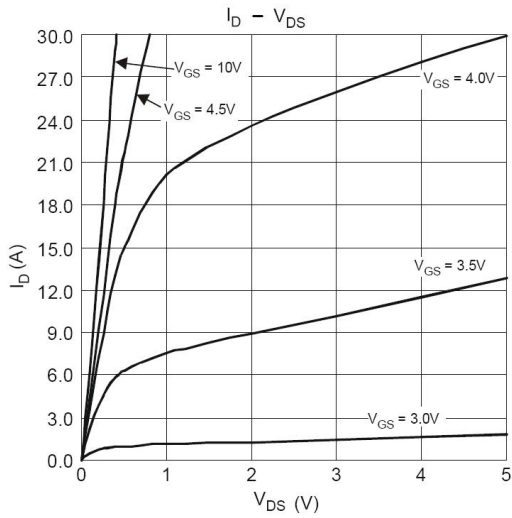
## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Capacitance(note9)	$C_{iss}$	$V_{DS}=30V$ $V_{GS}=0V$ $f=1.0MHz$		864		pF
Output Capacitance(note9)	$C_{oss}$			282		
Reverse Transfer Capacitance(note9)	$C_{rss}$			27		
Gate- Resistance	$R_g$	$V_{DS}=0V$ $V_{GS}=0V$ $f=1MHz$		1.3		$\Omega$
Total Gate Charge( $V_{GS} = 10V$ )	$Q_g$	$V_{DD}=30V$ $I_D=10A$		8.4		nC
Total Gate Charge( $V_{GS} = 4.5V$ )	$Q_g$			17		
Gate-Source Charge	$Q_{gs}$			3.1		
Gate-Drain Charge	$Q_{gd}$			4.3		
Turn-On Delay Time(note9)	$t_{d(on)}$	$V_{GS}=10V$ $I_D=10A$ $R_G=6\Omega$ $V_{DS}=30V$		3.4		ns
Turn-On Rise Time(note9)	$t_r$			5.2		
Turn-Off Delay Time(note9)	$t_{d(off)}$			13		
Turn-Off Fall Time(note9)	$t_f$			7.0		
Reverse Recovery Time	$t_{rr}$	$I_F=10A$ $di/dt=100A/\mu S$		22		ns
Reverse Recovery Charge	$Q_{rr}$			11		nC

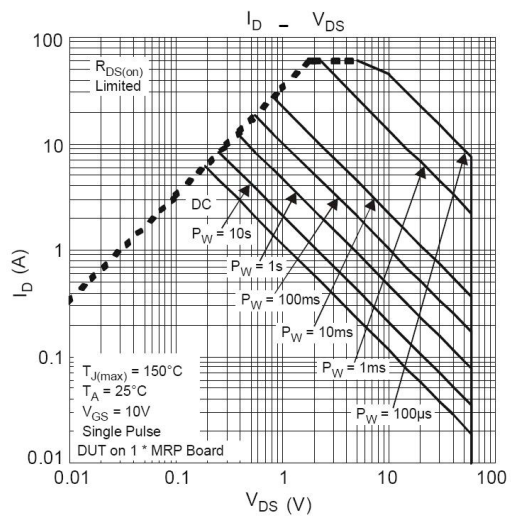
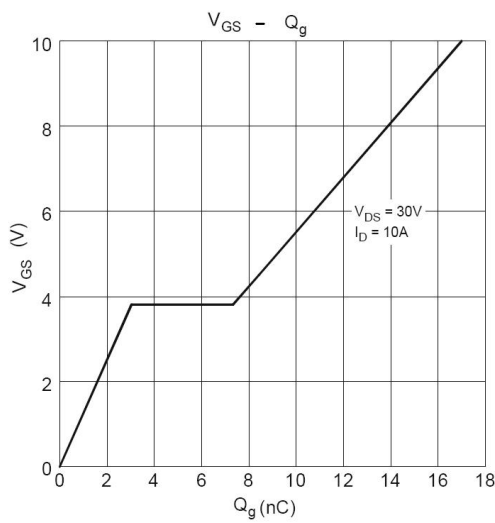
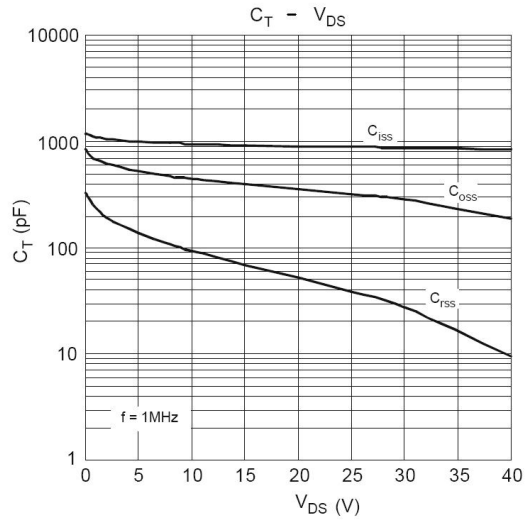
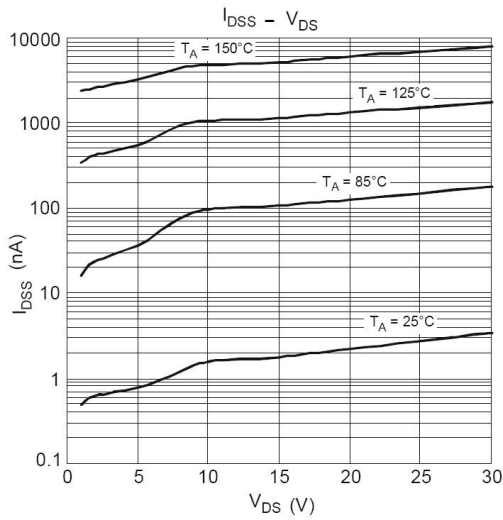
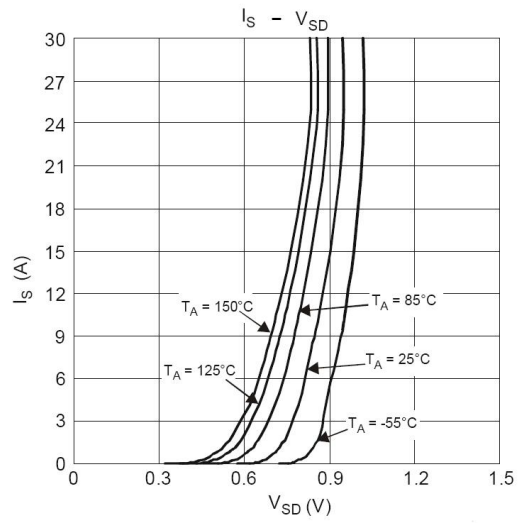
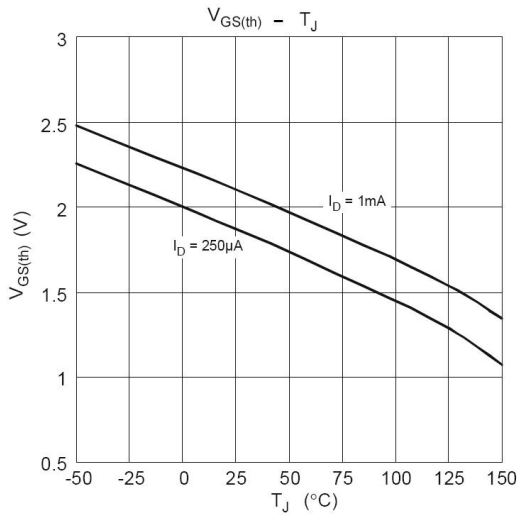
## Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = 25^\circ C$ .
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

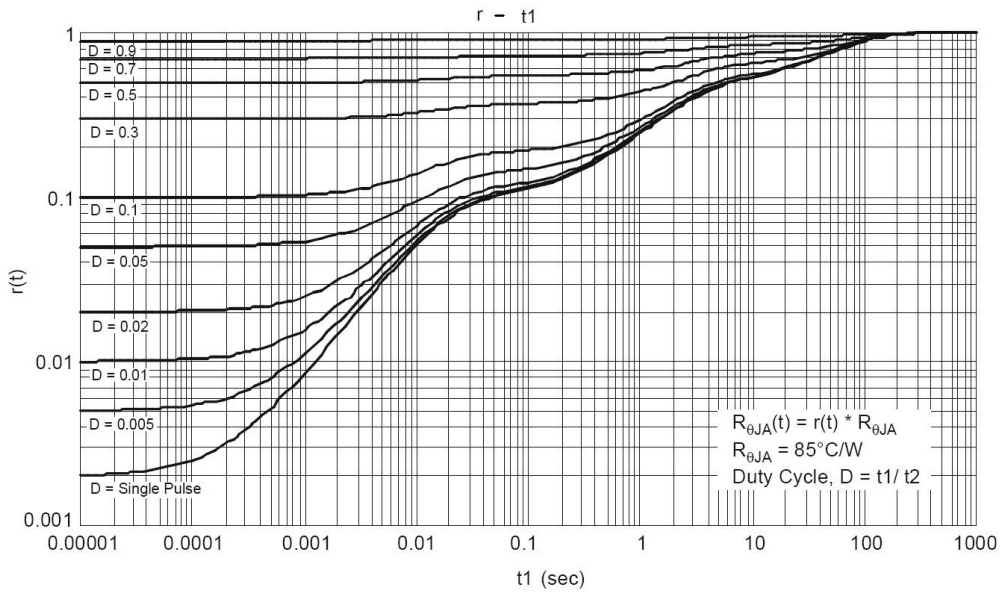
**电参数曲线图 / Electrical Characteristic Curve**



**电参数曲线图 / Electrical Characteristic Curve**



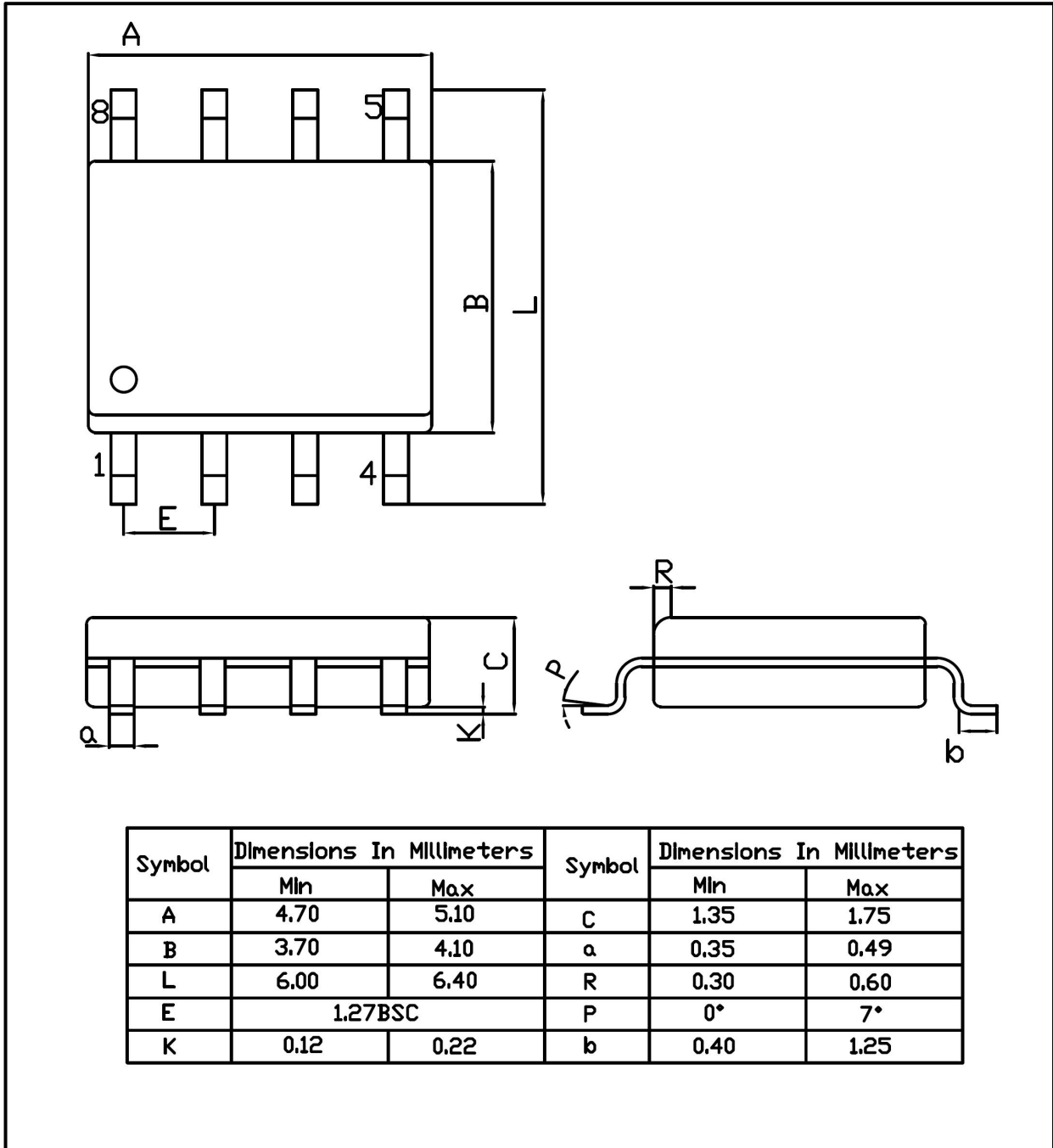
**电参数曲线图 / Electrical Characteristic Curve**



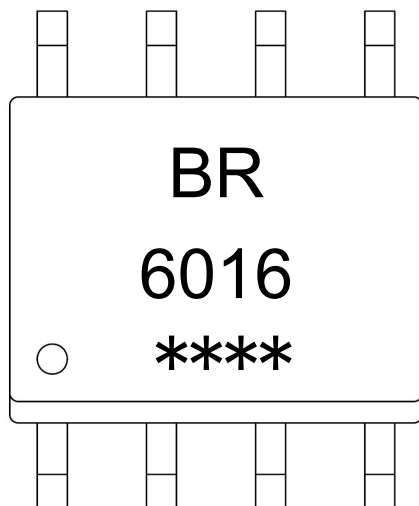
外形尺寸图 / Package Dimensions

SOP-8

Unit:mm



**印章说明 / Marking Instructions**



说明：

BR： 为公司代码

6016： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化。

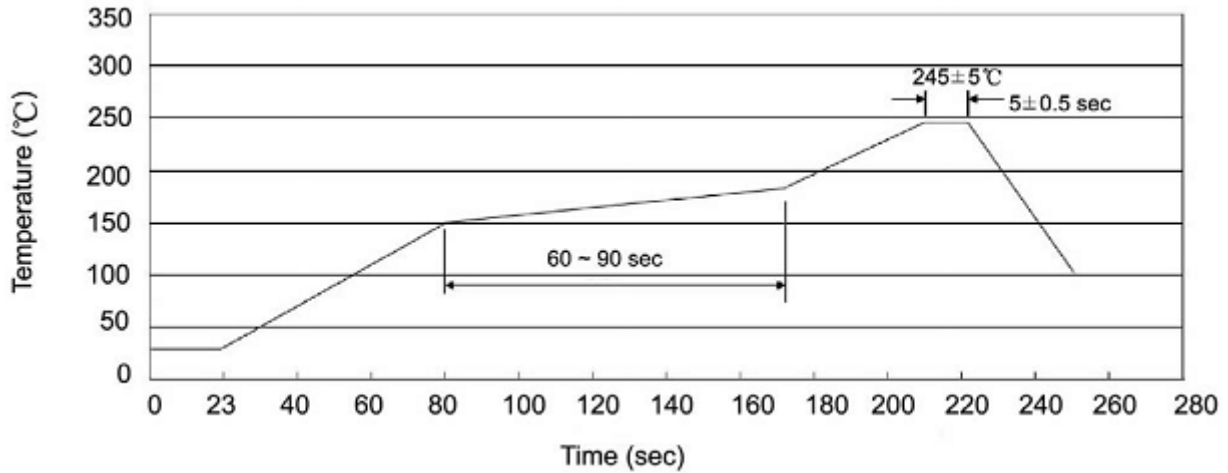
Note:

BR: Company Code.

6016: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.



**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 25~150°C，时间 60~90sec；
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	5	40,000	13" ×16	360×360×50	385×257×392

**使用说明 / Notices**